

| | Type | L # | Hits | Search Text | DBs | Time Stamp | Comments | Error Definition |
|---|------|-----|------|--|---|------------------|----------|------------------|
| 1 | BRS | L1 | 720 | LDMOS\$2 or LD-MOS\$2 or (LD adj MOS\$3) or LDMOSFET\$1 or LD-MOSFET\$1 or (LD adj MOSFET\$1) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2002/03/15 17:14 | | 0 |
| 2 | BRS | L2 | 51 | lateral\$4 adj diffus\$5 adj metal adj oxide adj semiconduct\$4 | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2002/03/15 17:16 | | 0 |
| 3 | BRS | L3 | 60 | lateral\$4 adj diffus\$5 adj (MOSS\$3 or MOSFET\$1) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2002/03/15 17:16 | | 0 |
| 4 | BRS | L4 | 479 | LDDMOSS\$2 or LDD-MOSS\$2 or (LDD adj MOSS\$3) or LDDMOSFET\$1 or LDD-MOSFET\$1 or (LDD adj MOSFET\$1) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2002/03/15 17:17 | | 0 |
| 5 | BRS | L5 | 74 | (lateral\$4 adj double adj diffus\$5 adj metal adj oxide adj semiconductor\$4) or (lateral\$4 adj double-diffus\$5 adj metal adj oxide adj semiconductor\$4) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2002/03/15 17:19 | | 0 |
| 6 | BRS | L6 | 178 | lateral\$4 adj double adj diffus\$5 adj (MOSS\$3 or MOSFET\$1) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2002/03/15 17:20 | | 0 |
| 7 | BRS | L7 | 249 | lateral\$4 near7 (metal adj oxide adj semiconductor\$4) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2002/03/15 17:21 | | 0 |

BEST AVAILABLE COPY

| | Type | L # | Hits | Search Text | DBs | Time Stamp | Comments | Error Definition |
|----|------|-----|------|---|---|---------------------|----------|------------------|
| 8 | BRS | L8 | 2322 | lateral\$4 near7 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2002/03/15 17:27 | | 0 |
| 9 | BRS | L9 | 10 | LDPMOS\$2 or LD-PMOSS\$2 or (LD adj PMOS\$3) or LDPMOSFET\$1 or LD-PMOSFET\$1 or (LD adj PMOSFET\$1) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2002/03/15 17:24 | | 0 |
| 10 | BRS | L10 | 5 | LDNMOSS\$2 or LD-NMOS\$2 or (LD adj NMOS\$3) or LDNMOSFET\$1 or LD-NMOSFET\$1 or (LD adj NMOSFET\$1) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2002/03/15 17:25 | | 0 |
| 11 | BRS | L11 | 455 | lateral\$4 near7 (DMOS or DMOSFET\$1) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2002/03/15 17:26 | | 0 |
| 12 | BRS | L12 | 8141 | lateral\$4 adj8 (MOS or MOSFET\$1 or NMOS or NMOSFET\$1 or PMOS or PMOSFET\$1 or FET\$1 or transistor\$1 or IGFET\$1 or (insulat\$5 adj gate adj field adj effect adj transistor\$1)) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2002/03/15 17:30 | | 0 |
| 13 | BRS | L13 | 9373 | 1 or 2 or 3 or 4 or 5 or 6 or 7 or 8 or 9 or 10 or 11 or 12 | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2002/03/15 17:32 | | 0 |

| | Type | L # | Hits | Search Text | DBs | Time Stamp | Comments | Error Definition | Error Definitors |
|----|------|-----|--------|---|---|------------------|----------|------------------|------------------|
| 14 | BRS | L14 | 152308 | (gate\$1 or electrode\$1) and source\$1 and drain\$1 | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2002/03/15 17:33 | | | 0 |
| 15 | BRS | L15 | 140917 | (field adj (oxide\$1 or isolat\$5) or LOCSS\$2 or trench\$2 or STI\$1 or (shallow adj trench\$2 adj isolat\$5)) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2002/03/15 17:36 | | | 0 |
| 16 | BRS | L16 | 1922 | 13 and 14 and 15 | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2002/03/15 17:36 | | | 0 |
| 17 | BRS | L17 | 15865 | (amorphous or amorph\$9) near3 (region\$1 or area\$1 or part\$1 or portion\$1 or element\$1) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2002/03/15 17:54 | | | 0 |
| 18 | BRS | L18 | 39181 | (amorphous or amorph\$9) near3 (layer\$1 or substrate\$1 or wafer\$1) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2002/03/15 18:05 | | | 0 |
| 19 | BRS | L19 | 30917 | (amorphous or amorph\$9) near3 film\$1 | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2002/03/15 18:11 | | | 0 |
| 20 | BRS | L20 | 67049 | 17 or 18 or 19 | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2002/03/15 18:11 | | | 0 |

| | Type | L # | Hits | Search Text | DBs | Time Stamp | Comments | Error Definition | Errors |
|----|------|-----|------|--|---|---------------------|----------|------------------|--------|
| 21 | BRS | L21 | 204 | 16 and 20 | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2002/03/15 18:12 | | | 0 |
| 22 | BRS | L22 | 5147 | implants\$8 adj (silicon or Si or "Si" or Ge or "Ge" or germanium) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2002/03/15 18:13 | | | 0 |
| 23 | BRS | L23 | 69 | 21 and 22 | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2002/03/15 18:25 | | | 0 |
| 24 | BRS | L24 | 498 | 20 same 22 | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2002/03/15 18:47 | | | 0 |
| 25 | BRS | L25 | 30 | 13 and 24 | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2002/03/15 18:26 | | | 0 |
| 26 | BRS | L26 | 330 | 20 with 22 | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2002/03/15 18:47 | | | 0 |
| 27 | BRS | L27 | 22 | 26 and 13 | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2002/03/15 18:50 | | | 0 |

BEST AVAILABLE COPIE

| Type | L # | Hits | Search Text | DBS | Time Stamp | Comments | Error Definition | Errors |
|--------|-----|-------|------------------------------|---|---------------------|----------|------------------|--------|
| 28 BRS | L28 | 23681 | 20 with (substrate or wafer) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2002/03/15 18:51 | | | 0 |
| 29 BRS | L29 | 244 | 22 same 28 | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2002/03/15 18:51 | | | 0 |
| 30 BRS | L30 | 16 | 13 and 29 | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB | 2002/03/15 18:52 | | | 0 |